

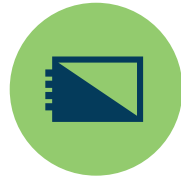
Silicon carbide performance inverter platform (SiC-PP)

Push the limits!



Lighter, more efficient, and more compact

Compact silicon carbide MOSFET performance inverter platform (SiC-PP)



Thanks to the advanced architecture of the SiC-PP, it is possible to satisfy a wide range of performance and use cases from ground transportation to aviation applications. The benefits of SiC semiconductors have been optimally leveraged to ensure the best performance-to-weight-to-cost ratio.

Full SiC-PP

Key features

- DC supply voltage up to 950 V_{DC}
- Phase current up to 600 A_{RMS}
- f_{PWM} up to 100 kHz
- Very compact
- Light weight 4.8 kg
- 3 or 6 phases



The full SiC-PP: one platform, three models, a wide range of use cases



Regular

- DC supply voltage up to 850 V_{DC}*
- Phase current up to 360 A_{RMS}
- f_{PWM} up to 100 kHz
- Very compact, 310 x 260 x 105 mm
- Weight 4.8 kg
- 3 phases



High Power

- DC supply voltage up to 950 V_{DC}
- Phase current up to 600 A_{RMS}
- f_{PWM} up to 20 kHz
- Very compact, 420 x 300 x 105 mm
- Weight 10.7 kg
- 3 phases



Double

- DC supply voltage up to 950 V_{DC}
- Phase current up to 360 A_{RMS}
- f_{PWM} up to 55 kHz
- Very compact, 420 x 300 x 105 mm
- Weight 10.7 kg
- 6 phases

* Limited to this voltage by the connector specification. 950 V_{DC} is applicable on custom design.